

ABSTRACT

A method of forming air gaps surrounding conductors in a dielectric layer, the dielectric layer comprising, for example, part of the interconnect structure of an integrated circuit device. The air gaps are formed, in part, by depositing a sacrificial material within a trench and/or via that have been formed in a dielectric layer, and the sacrificial material is ultimately removed after metal deposition to create the air gaps. A porous dielectric cap may be deposited over the dielectric layer, and the sacrificial material may be removed through this porous dielectric layer. Other embodiments are described and claimed.